

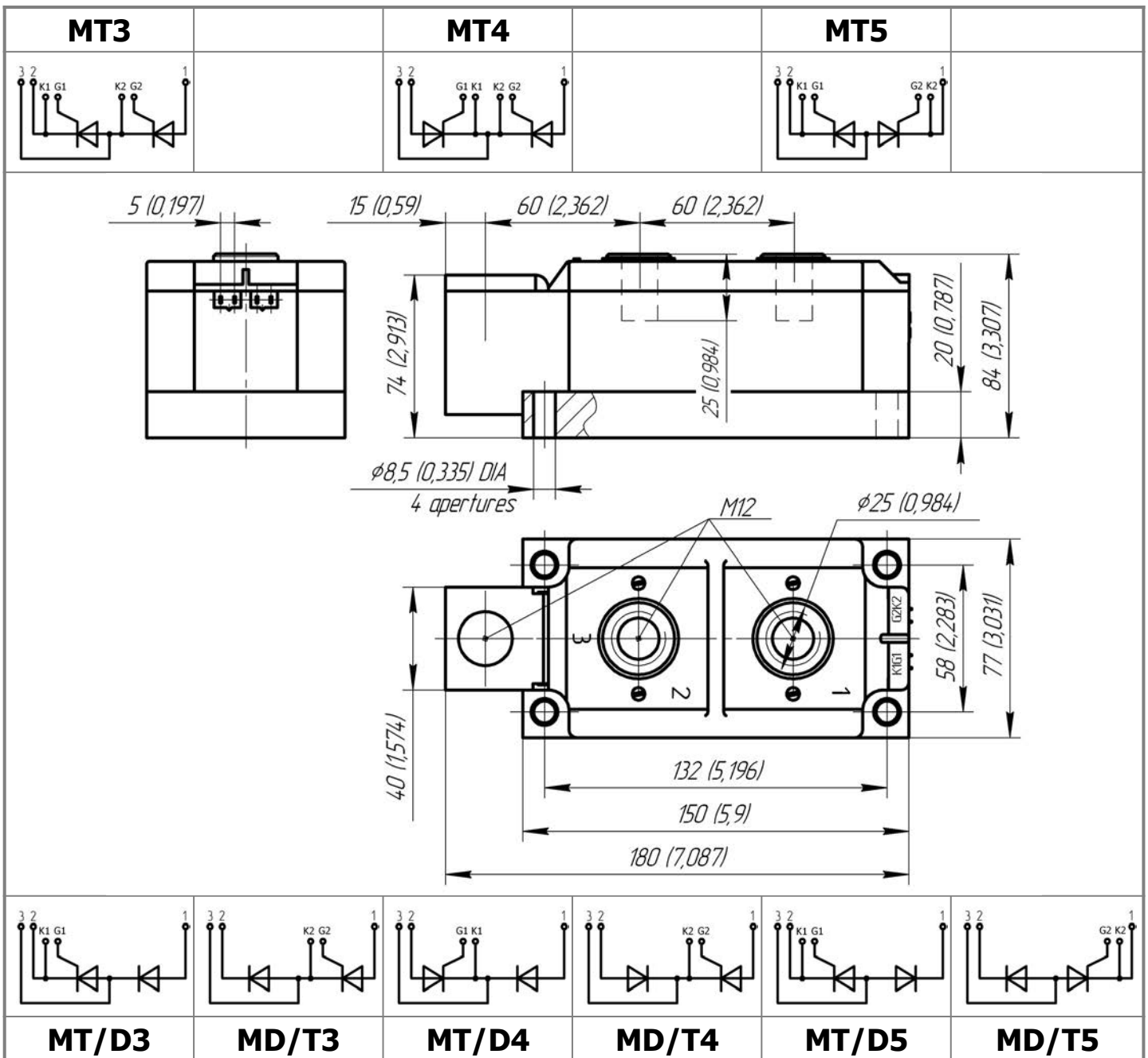


Thyristor Modules

MTx-740-24-D



Mean on-state current		I_{TAV}	740 A
Repetitive peak off-state voltage		V_{DRM}	2000...2400 V
Repetitive peak reverse voltage		V_{RRM}	
Turn-off time		t_q	200 μ s
V_{DRM}, V_{RRM}, V	2000	2200	2400
Voltage code	20	22	24
$T_j, ^\circ C$	-40...+125		



MAXIMUM ALLOWABLE RATINGS

Symbols and parameters		Units	Values	Test conditions
ON-STATE				
I_{TAV}	Maximum allowable mean on-state current	A	740 644	$T_c=77\text{ }^\circ\text{C}$; $T_c=85\text{ }^\circ\text{C}$; 180° half-sine wave; 50 Hz
I_{TRMS}	RMS on-state current	A	1162	$T_c=77\text{ }^\circ\text{C}$; 180° half-sine wave; 50 Hz
I_{TSM}	Surge on-state current	kA	29.0 33.0	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^\circ\text{C}$ 180° half-sine wave; $t_p=10\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt \geq 1\text{ A}/\mu\text{s}$
			30.0 35.0	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^\circ\text{C}$ 180° half-sine wave; $t_p=8.3\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt \geq 1\text{ A}/\mu\text{s}$
I^2t	Safety factor	$\text{A}^2\text{s}\cdot 10^3$	4200 5400	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^\circ\text{C}$ 180° half-sine wave; $t_p=10\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt \geq 1\text{ A}/\mu\text{s}$
			3700 5000	$T_j=T_{j\text{ max}}$ $T_j=25\text{ }^\circ\text{C}$ 180° half-sine wave; $t_p=8.3\text{ ms}$; single pulse; $V_D=V_R=0\text{ V}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt \geq 1\text{ A}/\mu\text{s}$
BLOCKING				
V_{DRM}, V_{RRM}	Repetitive peak off-state and Repetitive peak reverse voltages	V	2000...2400	$T_{j\text{ min}} < T_j < T_{j\text{ max}}$; 180° half-sine wave; 50 Hz; Gate open
V_{DSM}, V_{RSM}	Non-repetitive peak off-state and Non-repetitive peak reverse voltages	V	2100...2500	$T_{j\text{ min}} < T_j < T_{j\text{ max}}$; 180° half-sine wave; single pulse; Gate open
V_D, V_R	Direct off-state and Direct reverse voltages	V	$0.6\cdot V_{DRM}$ $0.6\cdot V_{RRM}$	$T_j=T_{j\text{ max}}$; Gate open
TRIGGERING				
I_{FGM}	Peak forward gate current	A	8	$T_j=T_{j\text{ max}}$
V_{RGM}	Peak reverse gate voltage	V	5	
P_G	Gate power dissipation	W	4	$T_j=T_{j\text{ max}}$ for DC gate current
SWITCHING				
$(di_T/dt)_{\text{crit}}$	Critical rate of rise of on-state current non-repetitive ($f=1\text{ Hz}$)	$\text{A}/\mu\text{s}$	2000	$T_j=T_{j\text{ max}}$; $V_D=0.67\cdot V_{DRM}$; $I_{TM}=5000\text{ A}$; Gate pulse: $I_G=2\text{ A}$; $t_{GP}=50\text{ }\mu\text{s}$; $di_G/dt \geq 2\text{ A}/\mu\text{s}$
THERMAL				
T_{stg}	Storage temperature	$^\circ\text{C}$	-40...+50	
T_j	Operating junction temperature	$^\circ\text{C}$	-40...+125	
$T_{c\text{ op}}$	Operating temperature	$^\circ\text{C}$	-40...+125	
MECHANICAL				
a	Acceleration under vibration	m/s^2	50	

CHARACTERISTICS

Symbols and parameters		Units	Values	Conditions	
ON-STATE					
V_{TM}	Peak on-state voltage, max	V	1.55	$T_j=25\text{ °C}; I_{TM}=3140\text{ A}$	
$V_{T(TO)}$	On-state threshold voltage, max	V	0.865	$T_j=T_{j\text{ max}};$	
r_T	On-state slope resistance, max	mΩ	0.238	$0.5\pi I_{TAV} < I_T < 1.5\pi I_{TAV}$	
I_L	Latching current, max	mA	1500	$T_j=25\text{ °C}; V_D=12\text{ V};$ Gate pulse: $I_G=2\text{ A};$ $t_{GP}=50\text{ μs}; di_G/dt\geq 1\text{ A/μs}$	
I_H	Holding current, max	mA	300	$T_j=25\text{ °C};$ $V_D=12\text{ V};$ Gate open	
BLOCKING					
I_{DRM}, I_{RRM}	Repetitive peak off-state and Repetitive peak reverse currents, max	mA	150 4.00	$T_j=T_{j\text{ max}}$ $T_j=25\text{ °C}$	$V_D=V_{DRM}; V_R=V_{RRM}$
$(dv_D/dt)_{crit}$	Critical rate of rise of off-state voltage ¹⁾ , min	V/μs	200, 320, 500, 1000, 1600, 2000, 2500	$T_j=T_{j\text{ max}};$ $V_D=0.67\cdot V_{DRM};$ Gate open	
TRIGGERING					
V_{GT}	Gate trigger direct voltage, max	V	3.00 2.50 1.50	$T_j=T_{j\text{ min}}$ $T_j=25\text{ °C}$ $T_j=T_{j\text{ max}}$	$V_D=12\text{ V}; I_D=3\text{ A};$ Direct gate current
I_{GT}	Gate trigger direct current, max	mA	400 300 150	$T_j=T_{j\text{ min}}$ $T_j=25\text{ °C}$ $T_j=T_{j\text{ max}}$	
V_{GD}	Gate non-trigger direct voltage, min	V	0.40	$T_j=T_{j\text{ max}};$ $V_D=0.67\cdot V_{DRM};$	
I_{GD}	Gate non-trigger direct current, min	mA	45.00	Direct gate current	
SWITCHING					
t_{gd}	Delay time, max	μs	1.00	$T_j=25\text{ °C}; V_D=1000\text{ V}; I_{TM}=I_{TAV};$ $di/dt=200\text{ A/μs};$	
t_{gt}	Turn-on time, max	μs	5.00	Gate pulse: $I_G=2\text{ A}; V_G=20\text{ V};$ $t_{GP}=50\text{ μs}; di_G/dt=2\text{ A/μs}$	
t_q	Turn-off time ²⁾ , max	μs	200	$dv_D/dt=50\text{ V/μs}; T_j=T_{j\text{ max}}; I_{TM}=I_{TAV};$ $di_R/dt=-10\text{ A/μs}; V_R=100\text{ V};$ $V_D=0.67\text{ }V_{DRM};$	
Q_{rr}	Total recovered charge, max	μC	2890	$T_j=T_{j\text{ max}}; I_{TM}=I_{TAV};$	
t_{rr}	Reverse recovery time, max	μs	35	$di_R/dt=-10\text{ A/μs};$	
I_{rr}	Reverse recovery current, max	A	165	$V_R=100\text{ V}$	
THERMAL					
R_{thjc}	Thermal resistance, junction to case			180° half-sine wave, 50 Hz	
	per module	°C/W	0.0250		
	per arm	°C/W	0.0500		
R_{thch}	Thermal resistance, case to heatsink				
	per module	°C/W	0.0080		
	per arm	°C/W	0.0160		
INSULATION					
V_{ISOL}	Insulation test voltage	kV	3.00	Sine wave, 50 Hz; RMS	t=60 sec
			3.60		t=1 sec
MECHANICAL					
M_1	Mounting torque (M8) ³⁾	Nm	9.00	Tolerance ± 15%	
M_2	Terminal connection torque (M12) ³⁾	Nm	18.00	Tolerance ± 15%	
m	Weight, max	g	4100		

PART NUMBERING GUIDE								NOTES																																	
MT	3	-	740	-	24	-	A2	P2										1) Critical rate of rise of off-state voltage																							
1	2		3		4		5	6										<table border="1"> <thead> <tr> <th>Symbol of Group</th> <th>P2</th> <th>K2</th> <th>E2</th> <th>A2</th> <th>T1</th> <th>P1</th> <th>M1</th> </tr> </thead> <tbody> <tr> <td>$(dv_D/dt)_{crit}, V/\mu s$</td> <td>200</td> <td>320</td> <td>500</td> <td>1000</td> <td>1600</td> <td>2000</td> <td>2500</td> </tr> </tbody> </table>								Symbol of Group	P2	K2	E2	A2	T1	P1	M1	$(dv_D/dt)_{crit}, V/\mu s$	200	320	500	1000	1600	2000	2500
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1. Thyristor module (MT) Thyristor – Diode module (MT/D) Diode – Thyristor module (MD/T)								2) Turn-off time ($dv_D/dt=50 V/\mu s$)																																	
2. Circuit Schematic: 3 – serial connection 4 – common Cathode 5 – common Anode								<table border="1"> <thead> <tr> <th>Symbol of group</th> <th>P2</th> </tr> </thead> <tbody> <tr> <td>$t_{off}, \mu s$</td> <td>200</td> </tr> </tbody> </table>								Symbol of group	P2	$t_{off}, \mu s$	200																						
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3. Average On-state Current, A 4. Voltage Code 5. Critical rate of rise of off-state voltage 6. Group of turn-off time ($dv_D/dt=50 V/\mu s$) 7. Package Type (M.D) 8. Ambient Conditions: N – Normal								3) The screws must be lubricated																																	

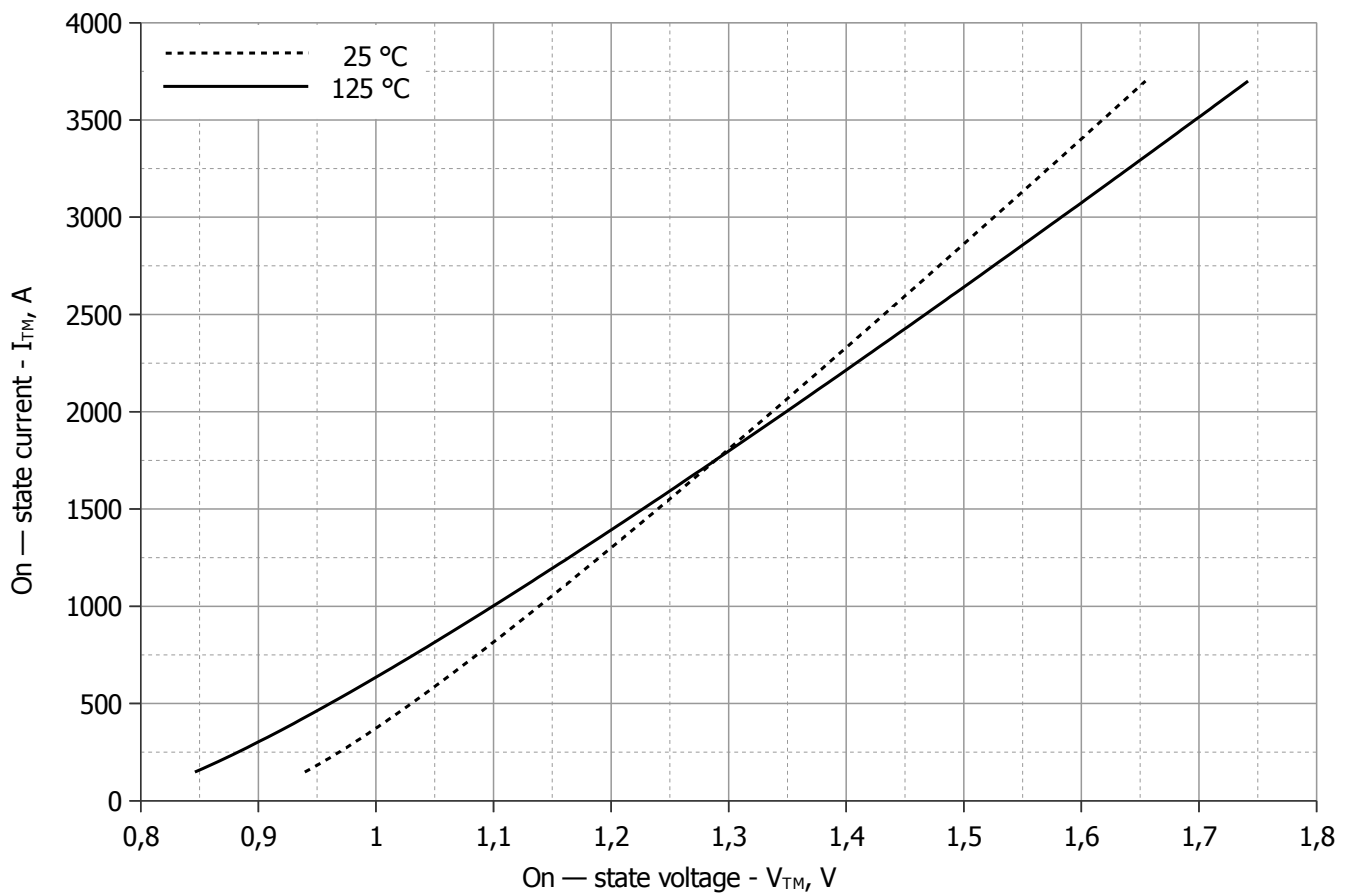


Fig 1 – On-state characteristics of Limit device

Analytical function for On-state characteristic:

$$V_T = A + B \cdot i_T + C \cdot \ln(i_T + 1) + D \cdot \sqrt{i_T}$$

	Coefficients for max curves	
	$T_j = 25^\circ\text{C}$	$T_j = T_{j,\text{max}}$
A	0.85316202	0.76837178
B	0.00015928	0.00018154
C	0.00606344	-0.00282265
D	0.00266640	0.00534063

On-state characteristic model (see Fig. 1)

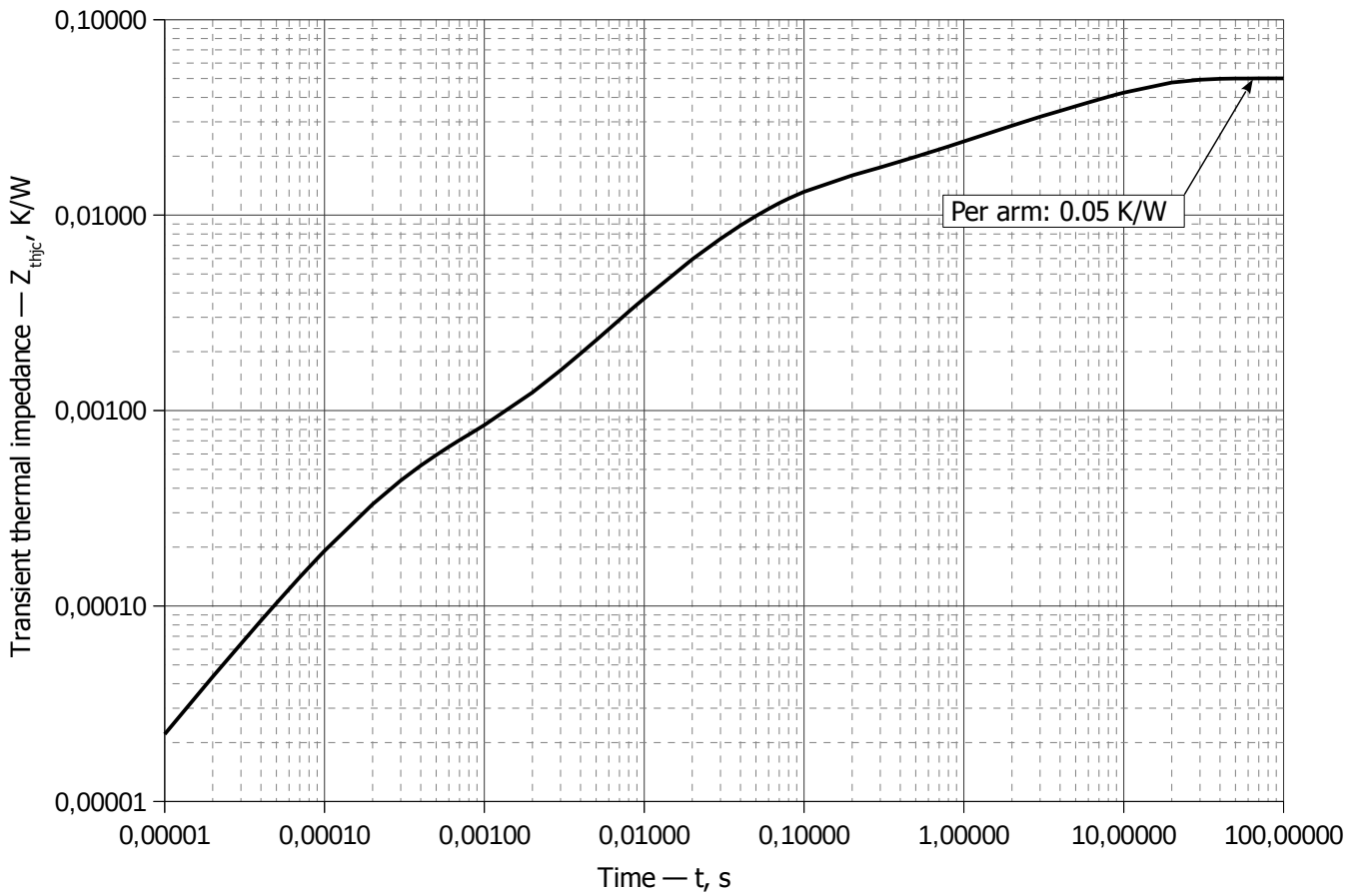


Fig 2 – Transient thermal impedance Z_{thjc} vs. time t

Analytical function for Transient thermal impedance junction to case Z_{thjc} for DC:

$$Z_{thjc} = \sum_{i=1}^n R_i \left(1 - e^{-\frac{t}{\tau_i}} \right)$$

Where $i = 1$ to n , n is the number of terms in the series.

t = Duration of heating pulse in seconds.

Z_{thjc} = Thermal resistance at time t .

R_i = Amplitude of p_{th} term.

τ_i = Time constant of r_{th} term.

i	1	2	3	4	5	6
R_i K/W	0.02506	0.009643	0.00348	0.009712	0.001719	0.0004399
τ_i s	8.474	1.11	0.2289	0.04529	0.009524	0.0002414

Transient thermal impedance junction to case Z_{thjc} model (see Fig. 2)

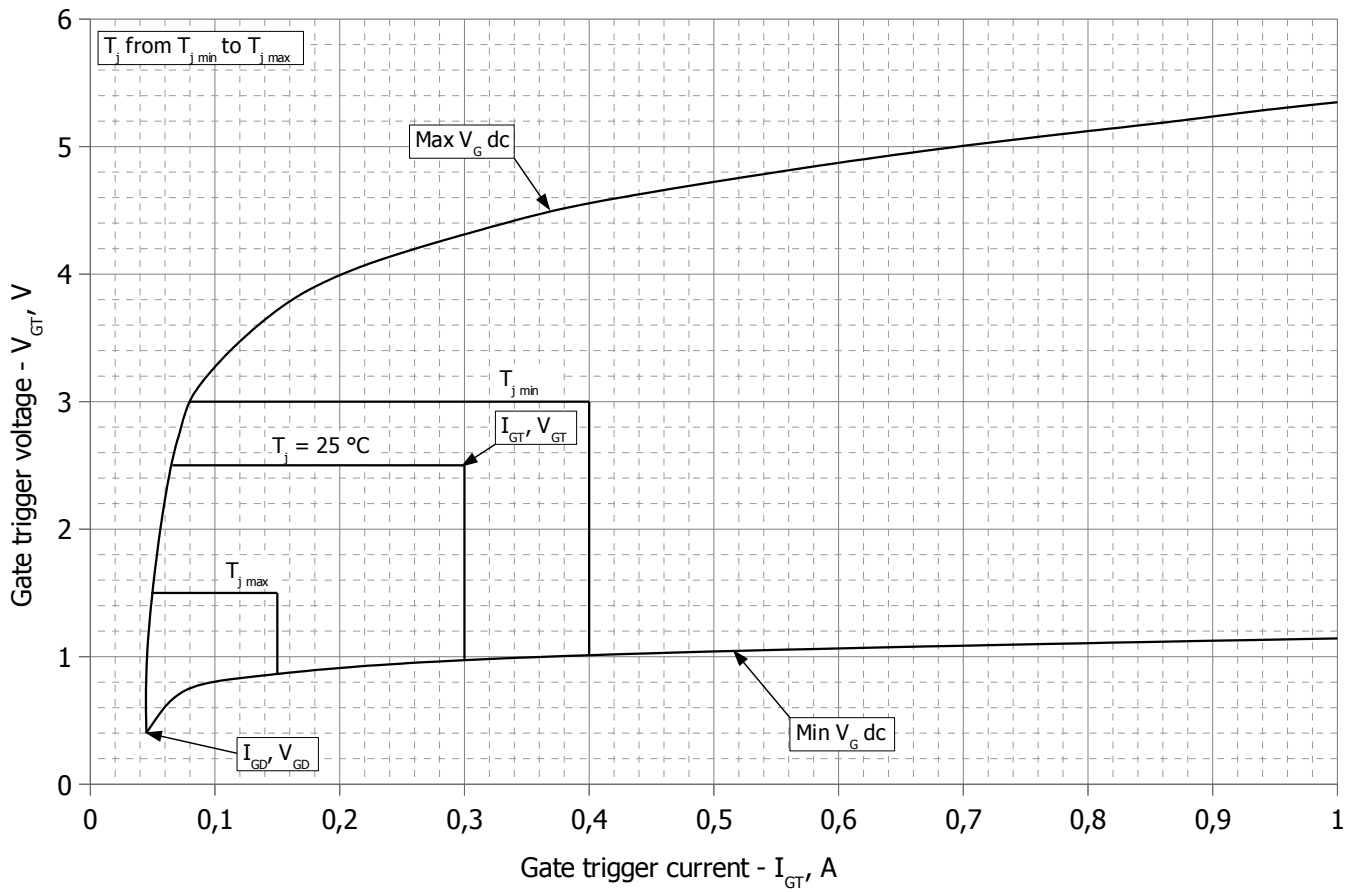


Fig 3 – Gate characteristics – Trigger limits

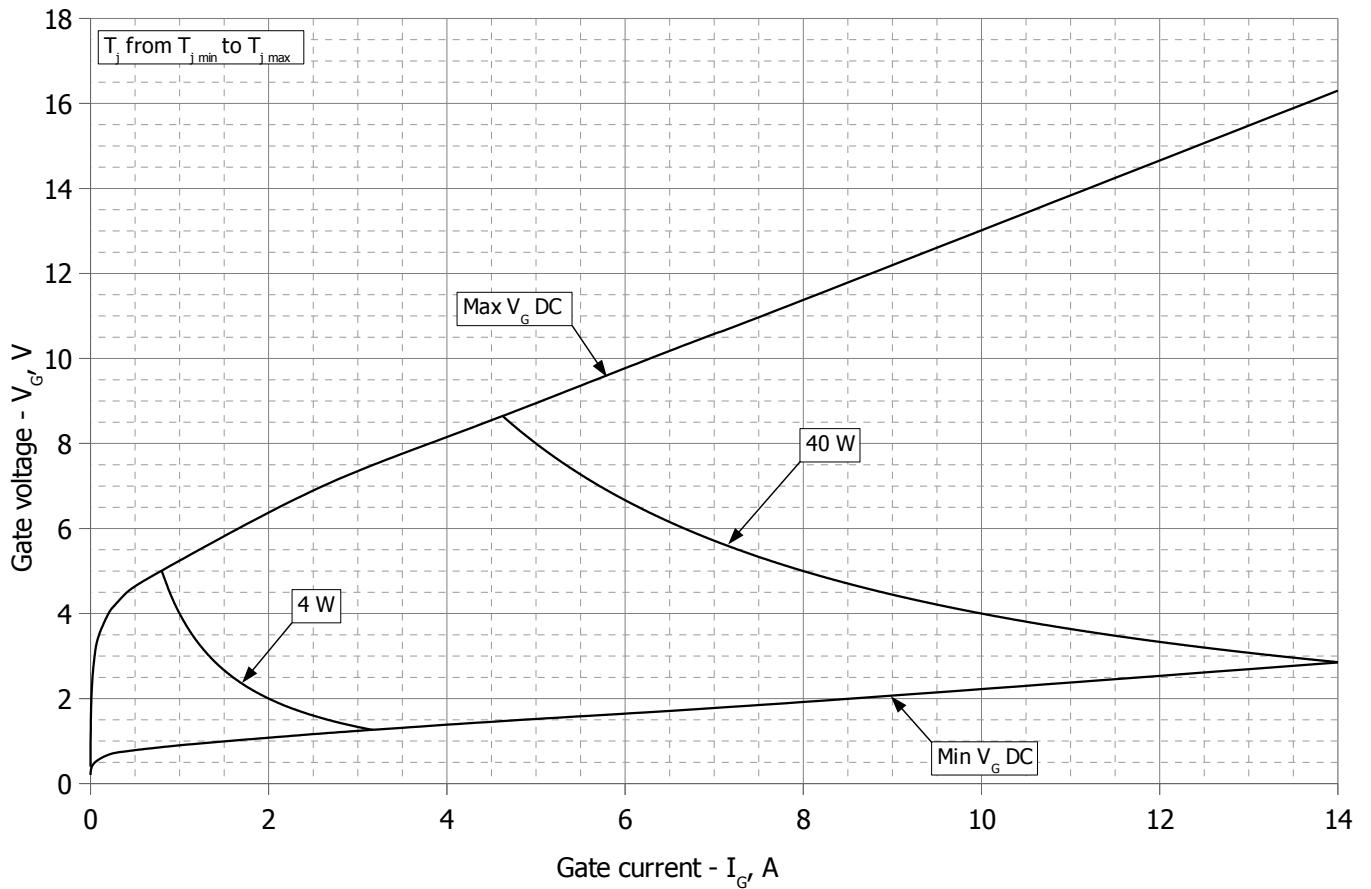


Fig 4 - Gate characteristics – Power curves

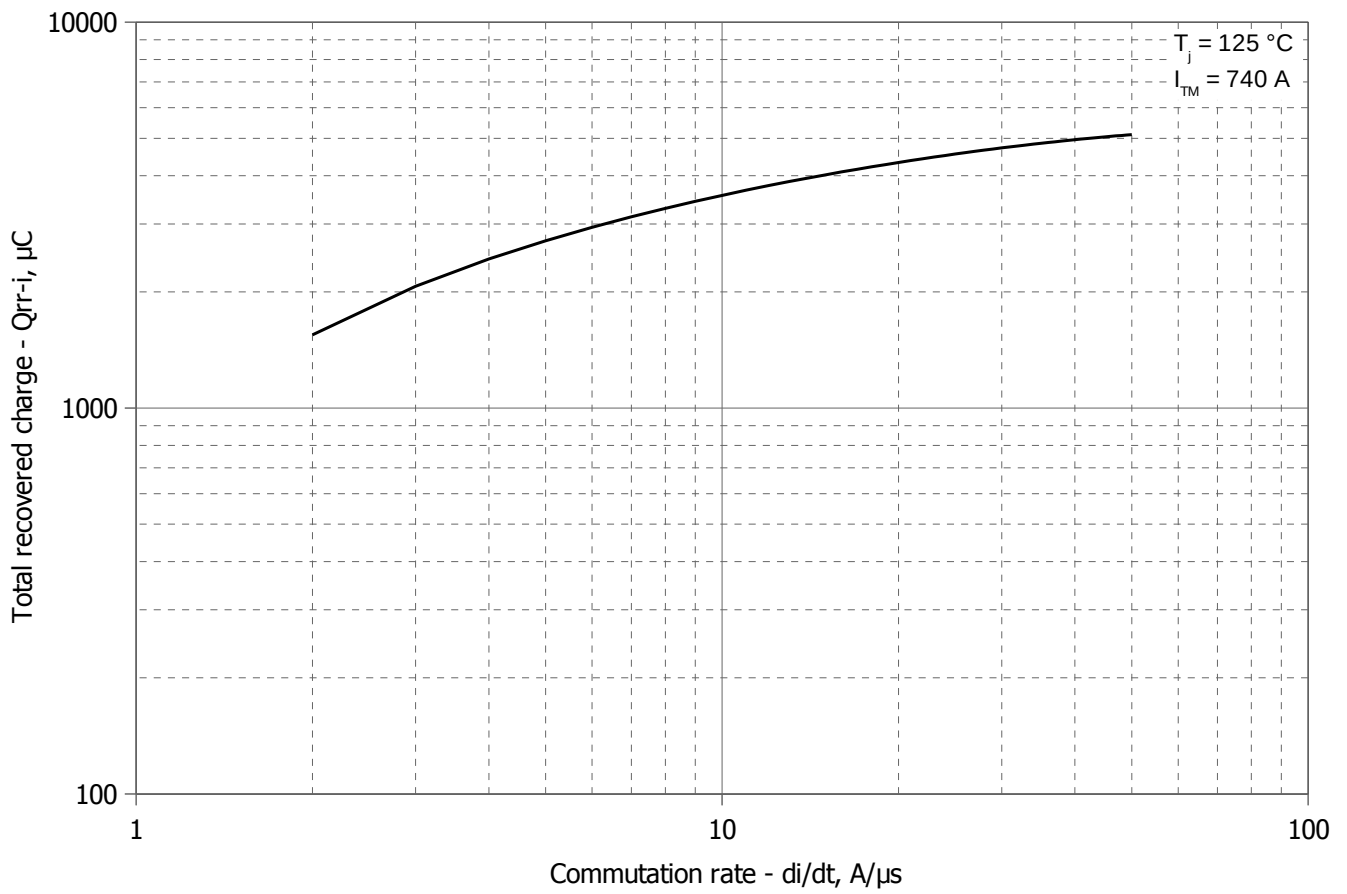


Fig 5 – Maximum recovered charge Q_{rr-i} (integral) vs. commutation rate di_R/dt

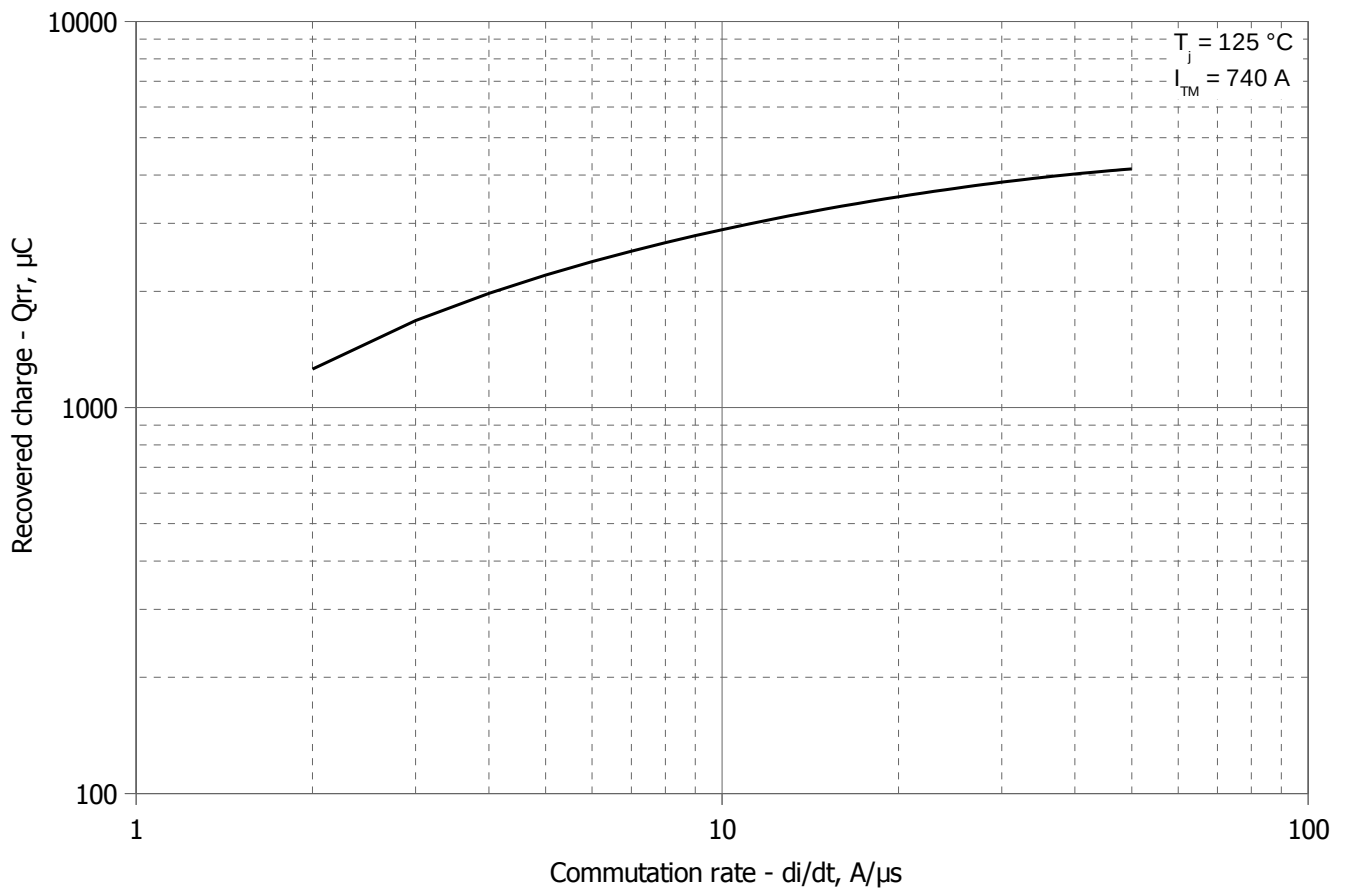


Fig 6 – Maximum recovered charge Q_{rr} vs. commutation rate di_R/dt (25% chord)

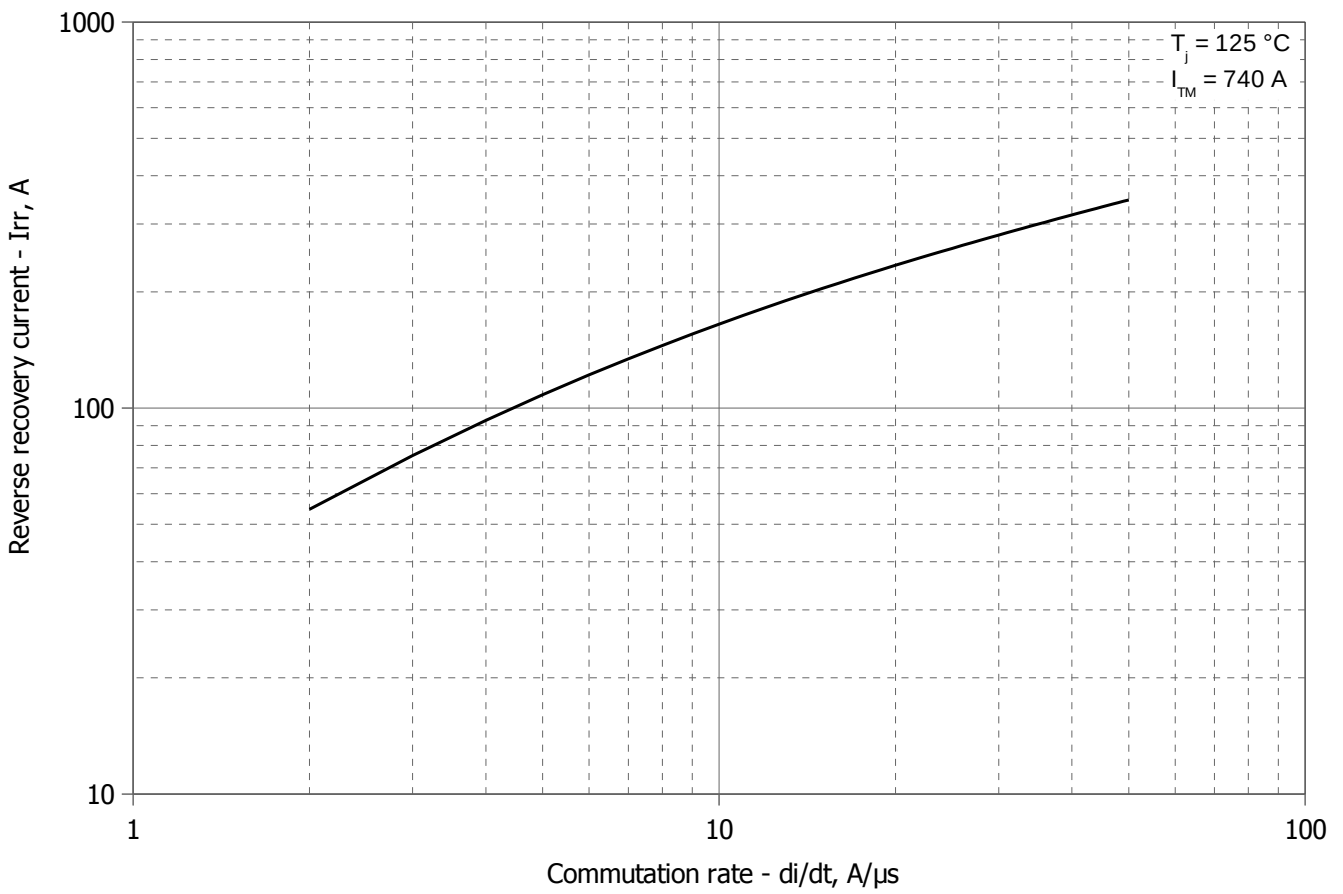


Fig 7 – Maximum reverse recovery current I_{rr} vs. commutation rate di_R/dt

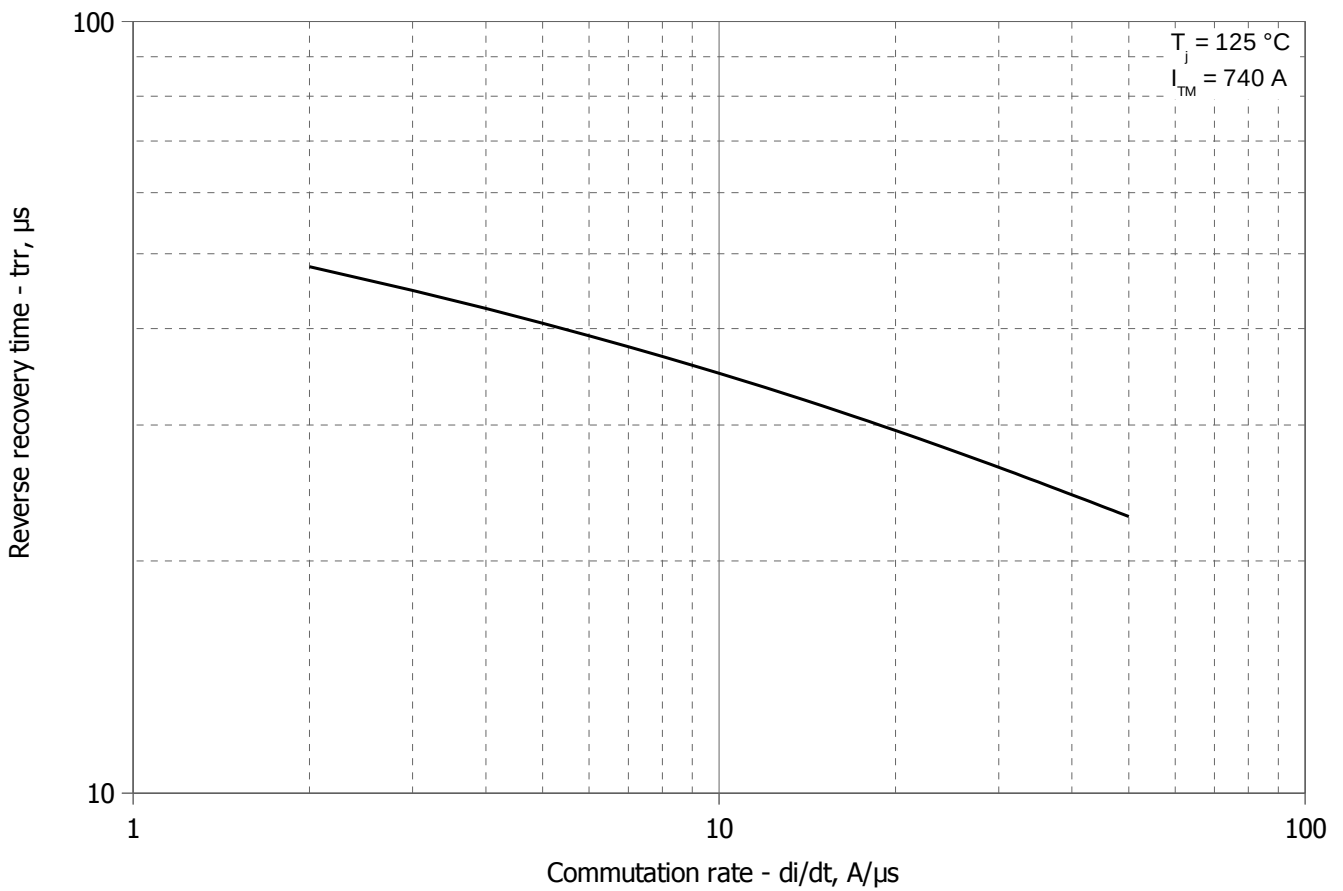


Fig 8 – Maximum recovery time t_{rr} vs. commutation rate di_R/dt (25% chord)

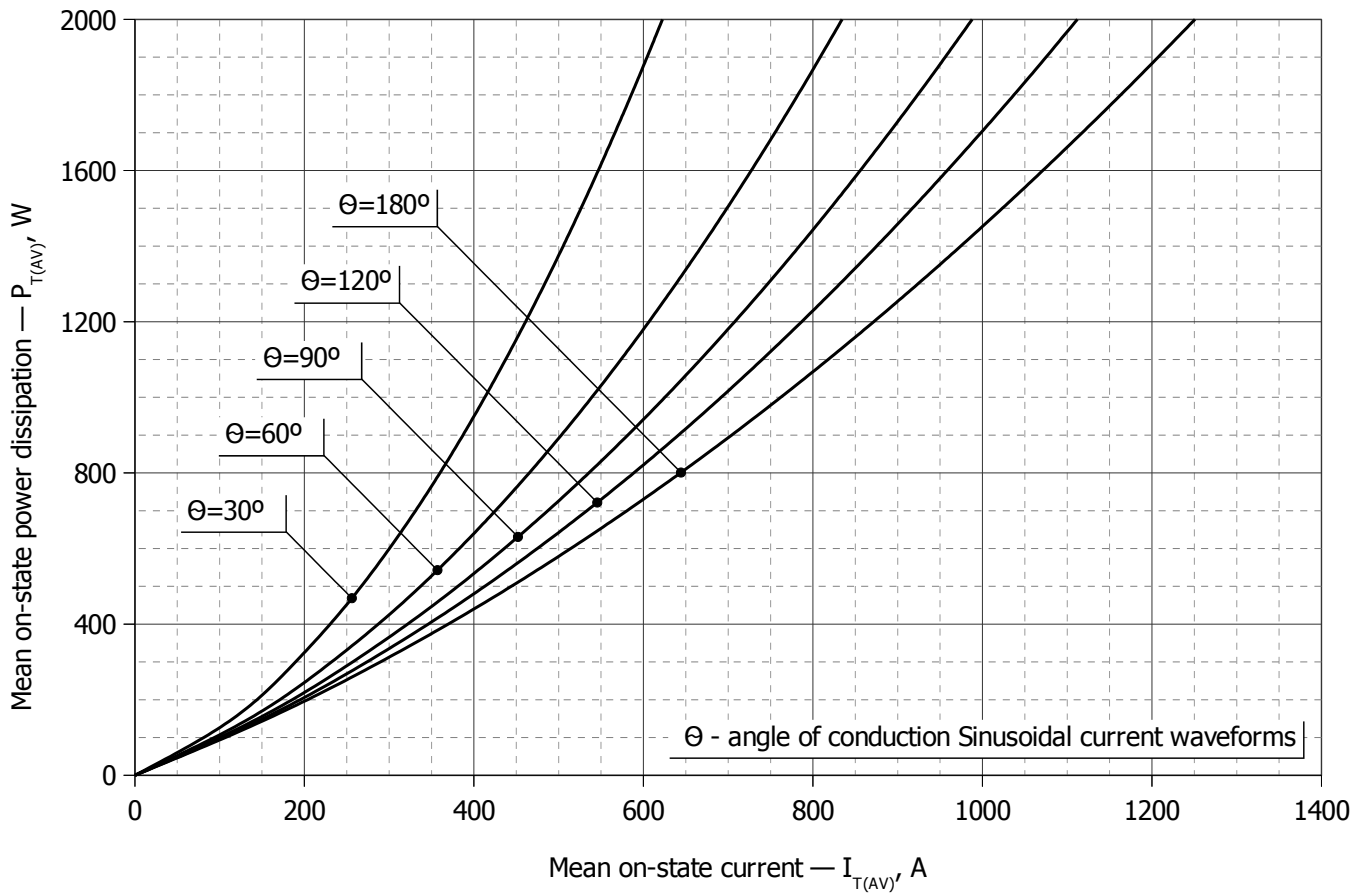


Fig. 9 - Mean on-state power dissipation P_{TAV} vs. mean on-state current I_{TAV} for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$, DSC)

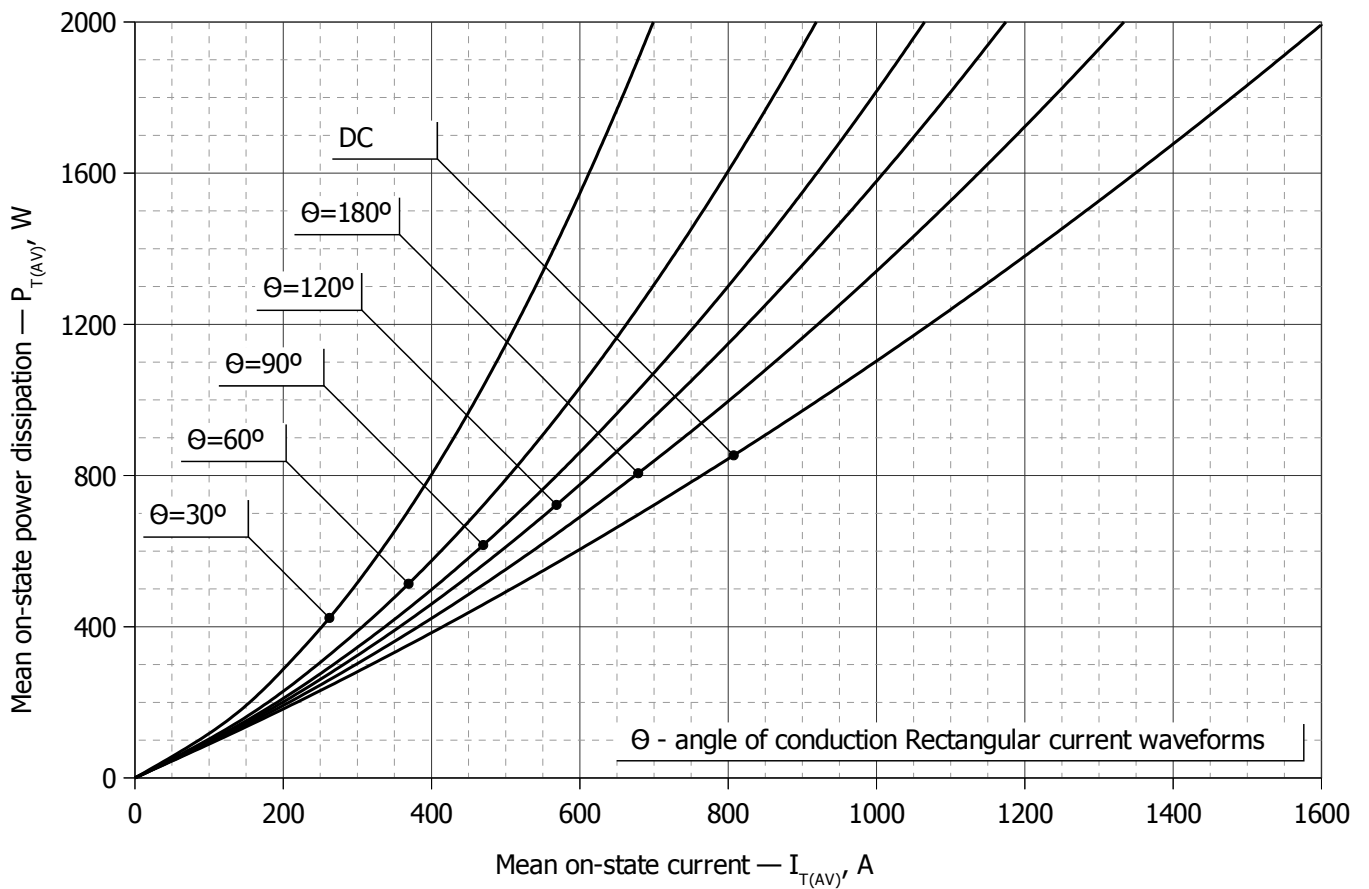


Fig. 10 - Mean on-state power dissipation P_{TAV} vs. mean on-state current I_{TAV} for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$, DSC)

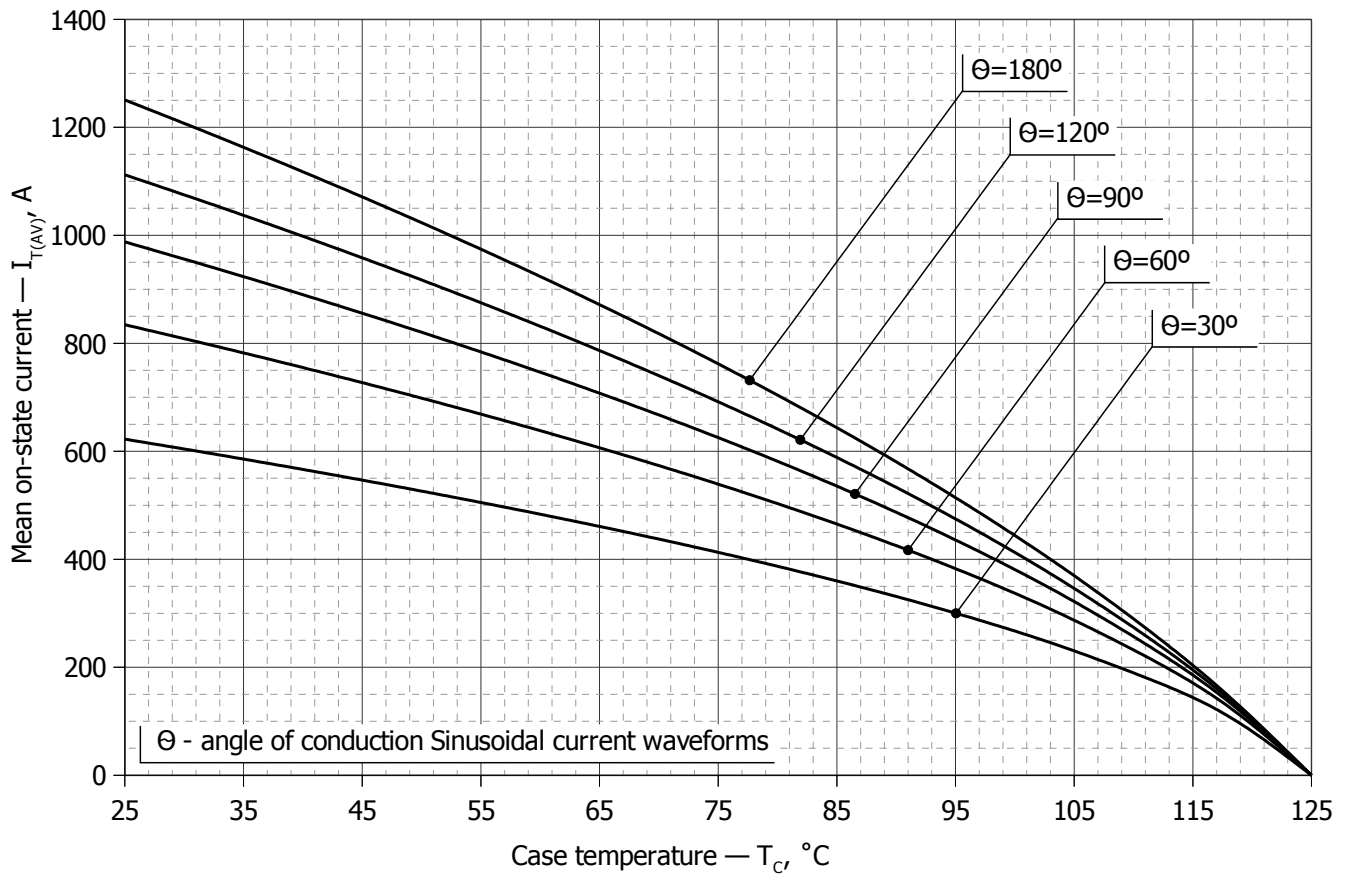


Fig. 11 – Mean on-state current I_{TAV} vs. case temperature T_c for sinusoidal current waveforms at different conduction angles ($f=50\text{Hz}$, DSC)

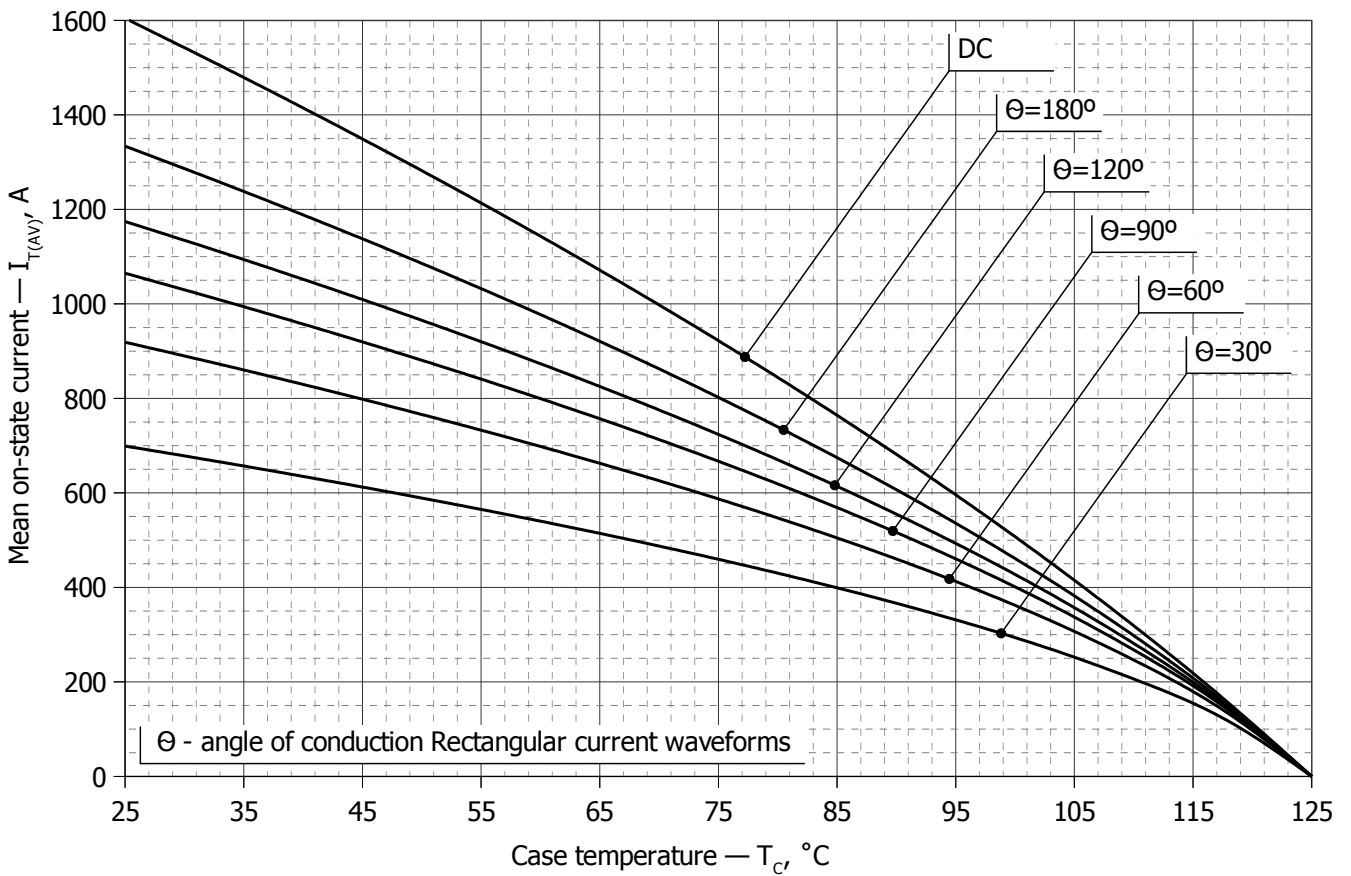


Fig. 12 - Mean on-state current I_{TAV} vs. case temperature T_c for rectangular current waveforms at different conduction angles and for DC ($f=50\text{Hz}$, DSC)

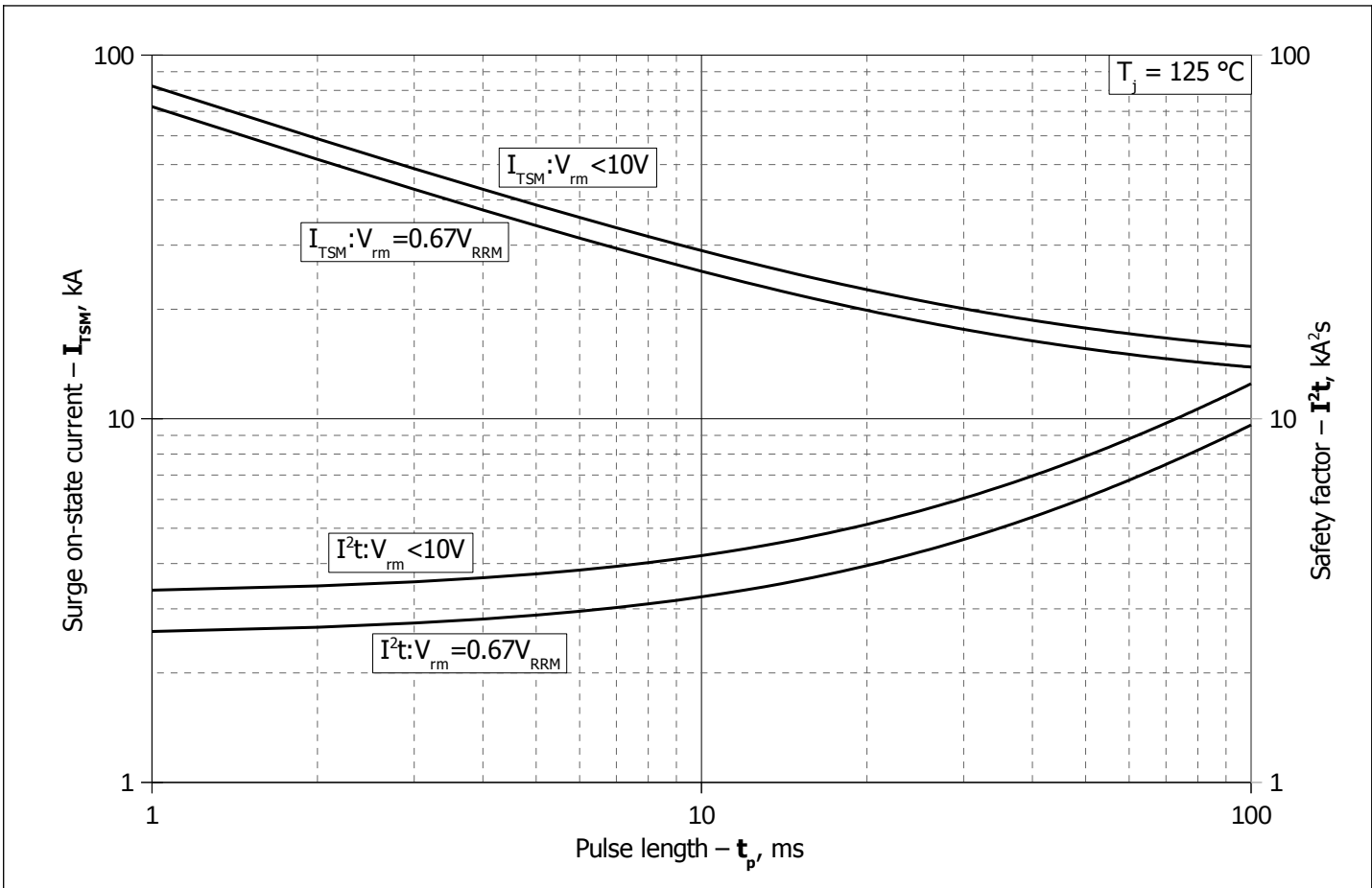


Fig. 13 – Maximum surge on-state current I_{TSM} and safety factor I^2t vs. pulse length t_p

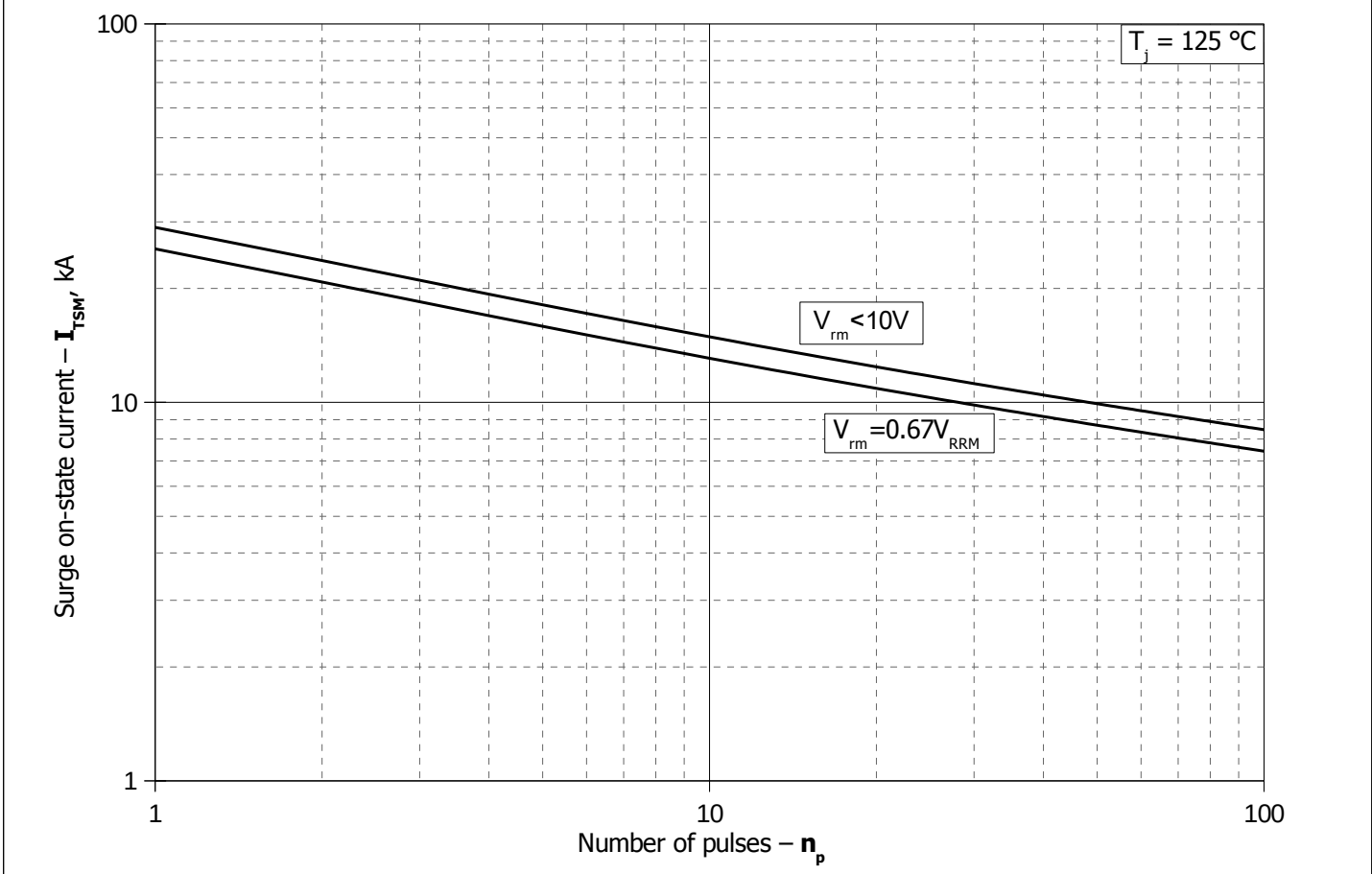


Fig. 14 - Maximum surge on-state current I_{TSM} vs. number of pulses n_p